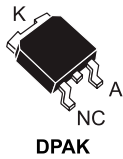
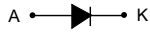


## Automotive 650 V power Schottky silicon carbide diode



### Features

- AEC-Q101 qualified
- No reverse recovery charge in application current range
- Switching behavior independent of temperature
- Recommended to PFC applications
- PPAP capable
- ECOPACK<sup>®</sup>2 compliant component

### Description

The SiC diode is an ultra-high performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Especially suited for use in PFC applications, this ST SiC diode will boost performance in hard switching conditions.

Product status	
STPSC6H065BY-TR	
Product summary	
Symbol	Value
$I_{F(AV)}$	6 A
$V_{RRM}$	650 V
$T_{j(max.)}$	175 °C

# 1 Characteristics

**Table 1. Absolute ratings (limiting values at 25 °C unless otherwise specified)**

Symbol	Parameter		Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage	$T_j = -40\text{ °C to } +175\text{ °C}$	650	V
$I_{F(RMS)}$	Forward rms current		22	A
$I_{F(AV)}$	Average forward current	$T_c = 145\text{ °C}^{(1)}$ , DC	6	A
$I_{FSM}$	Surge non repetitive forward current	$t_p = 10\text{ ms sinusoidal}$ , $T_c = 25\text{ °C}$	60	A
		$t_p = 10\text{ ms sinusoidal}$ , $T_c = 125\text{ °C}$	52	
		$t_p = 10\text{ }\mu\text{s square}$ , $T_c = 25\text{ °C}$	400	
$I_{FRM}$	Repetitive peak forward current	$T_c = 145\text{ °C}^{(1)}$ , $T_j = 175\text{ °C}$ , $\delta = 0.1$	23	A
$T_{stg}$	Storage temperature range		-55 to +175	°C
$T_j$	Operating junction temperature range <sup>(2)</sup>		-40 to +175	°C

1. Value based on  $R_{th(j-c)}$  max.

2.  $(dP_{tot}/dT_j) < (1/R_{th(j-a)})$  condition to avoid thermal runaway for a diode on its own heatsink.

**Table 2. Thermal parameters**

Symbol	Parameter	Typ. value	Max. value	Unit
$R_{th(j-c)}$	Junction to case	1.6	2.4	°C/W

**Table 3. Static electrical characteristics**

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
		$T_j$	$V_R$				
$I_R^{(1)}$	Reverse leakage current	$T_j = 25\text{ °C}$	$V_R = V_{RRM}$	-	5	60	$\mu\text{A}$
		$T_j = 150\text{ °C}$		-	50	250	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25\text{ °C}$	$I_F = 6\text{ A}$	-	1.45	1.65	V
		$T_j = 150\text{ °C}$		-	1.7	2.05	

1.  $t_p = 10\text{ ms}$ ,  $\delta < 2\%$

2.  $t_p = 500\text{ }\mu\text{s}$ ,  $\delta < 2\%$

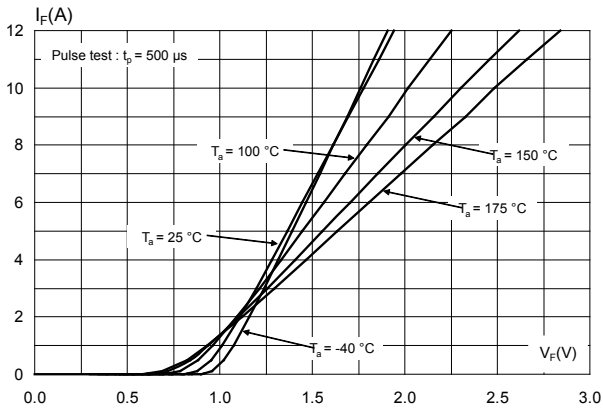
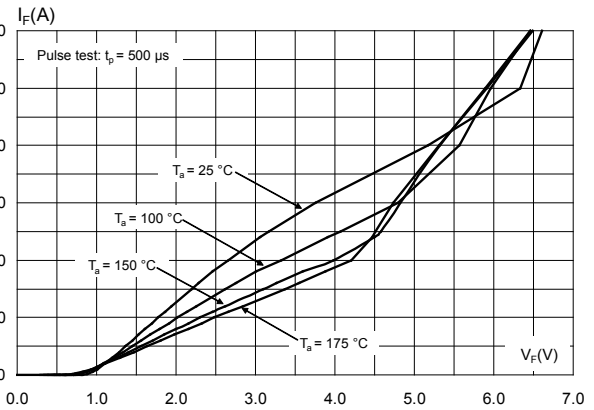
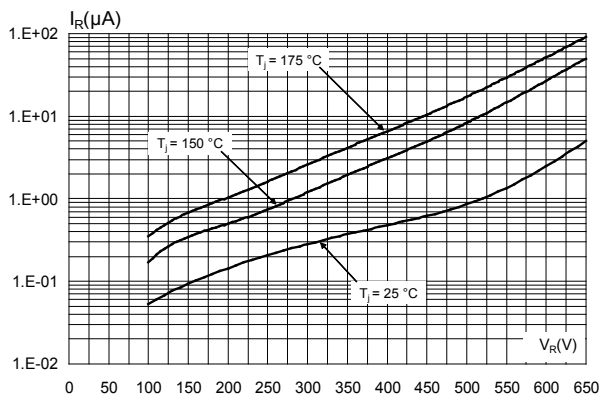
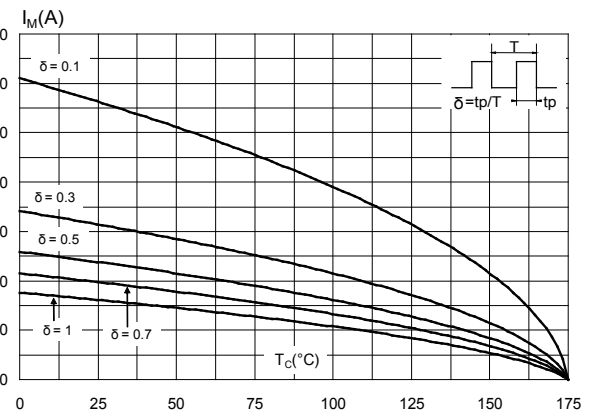
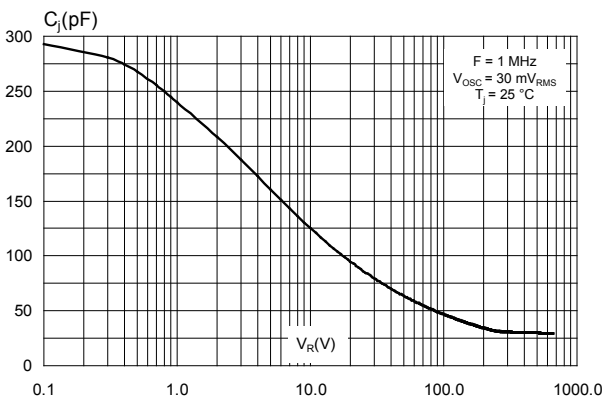
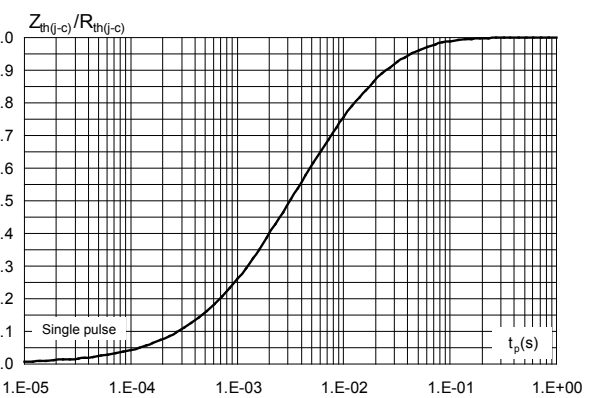
To evaluate the conduction losses, use the following equation:

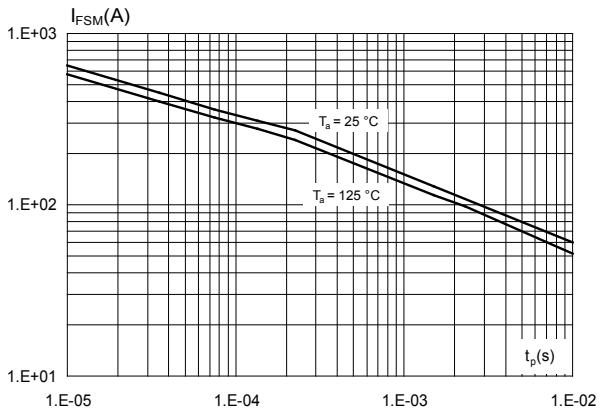
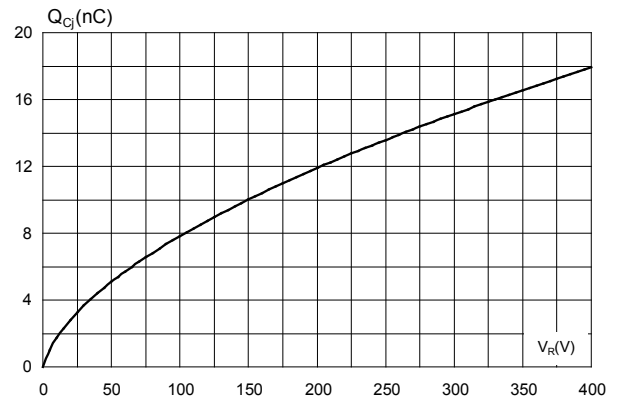
$$P = 0.972 \times I_{F(AV)} + 0.180 \times I_{F(RMS)}^2$$

**Table 4. Dynamic electrical characteristics**

Symbol	Parameter	Test conditions	Typ.	Unit
$Q_{cj}^{(1)}$	Total capacitive charge	$V_R = 400\text{ V}$	18	nC
$C_j$	Total capacitance	$V_R = 0\text{ V}$ , $T_c = 25\text{ °C}$ , $F = 1\text{ MHz}$	300	pF
		$V_R = 400\text{ V}$ , $T_c = 25\text{ °C}$ , $F = 1\text{ MHz}$	30	

1. Most accurate value for the capacitive charge:  $Q_{cj} = \int_0^{V_{OUT}} c_j(V_R) \times dV_R$

**1.1 Characteristics (curves)**
**Figure 1. Forward voltage drop versus forward current (typical values, low level)**

**Figure 2. Forward voltage drop versus forward current (typical values, high level)**

**Figure 3. Reverse leakage current versus reverse voltage applied (typical values)**

**Figure 4. Peak forward current versus case temperature**

**Figure 5. Junction capacitance versus reverse voltage applied (typical values)**

**Figure 6. Relative variation of thermal impedance junction to case versus pulse duration**


**Figure 7. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform)**

**Figure 8. Total capacitive charges versus reverse voltage applied (typical values)**


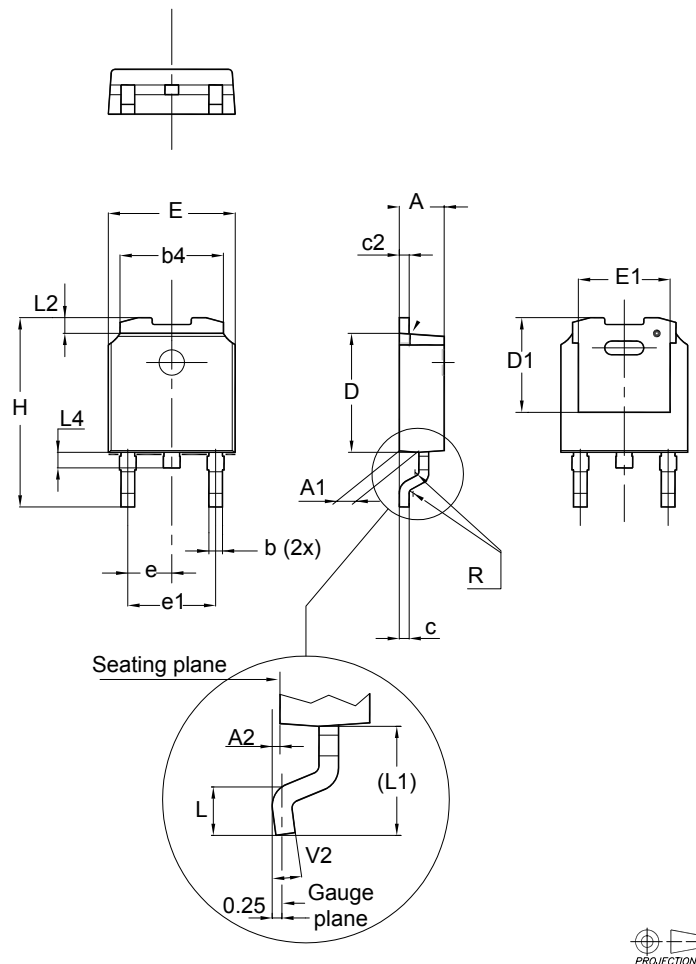
## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

### 2.1 DPAK package information

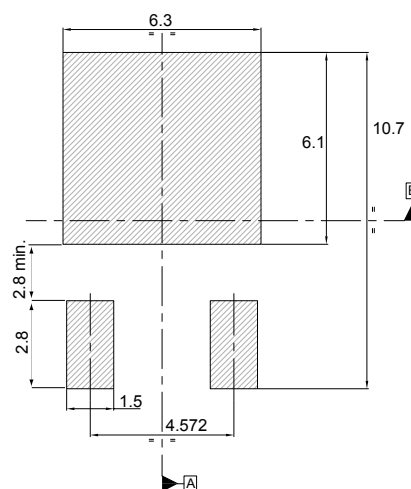
- Epoxy meets UL94, V0
- Cooling method: by conduction (C)

**Figure 9. DPAK package outline**



**Table 5. DPAK mechanical data**

Dim.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
b	0.64		0.90	0.025		0.035
b4	5.20		5.40	0.205		0.213
c	0.45		0.60	0.018		0.024
c2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
D1	4.95	5.10	5.25	0.195	0.201	0.207
E	6.40		6.60	0.252		0.260
E1	4.60	4.70	4.80	0.181	0.185	0.189
e	2.16	2.28	2.40	0.085	0.090	0.094
e1	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L	1.00		1.50	0.039		0.059
(L1)	2.60	2.80	3.00	0.102	0.110	0.118
L2	0.65	0.80	0.95	0.026	0.031	0.037
L4	0.60		1.00	0.024		0.039
R		0.20			0.008	
V2	0°		8°	0°		8°

**Figure 10. DPAK recommended footprint (dimensions are in mm)**

 The device must be positioned within  $\boxed{\text{M}} \boxed{0.05} \boxed{\text{A}} \boxed{\text{B}}$

### 3 Ordering Information

Table 6. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPSC6H065BY-TR	PSC6H 065Y	DPAK	0.32 g	2500	Tape and reel

## Revision history

**Table 7. Document revision history**

Date	Version	Changes
13-Mar-2018	1	Initial release.



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